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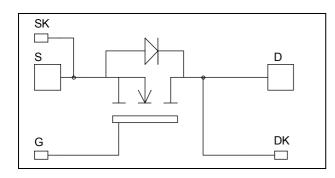






# Single Switch MOSFET Power Module

$$\begin{split} V_{DSS} &= 1000V \\ R_{DSon} &= 60 m \Omega \text{ typ @ Tj} = 25^{\circ} C \\ I_D &= 129 A \text{ @ Tc} = 25^{\circ} C \end{split}$$



#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Power MOS 7<sup>®</sup> FREDFETs
  - Low R<sub>DSon</sub>
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		1000	V
Ţ	Continuous Drain Current	$T_c = 25$ °C	129	
$I_D$	Continuous Drain Current	$T_c = 80$ °C	97	A
$I_{DM}$	Pulsed Drain current		516	
$V_{GS}$	Gate - Source Voltage		±30	V
R <sub>DSon</sub>	Drain - Source ON Resistance		70	mΩ
$P_{D}$	Maximum Power Dissipation $T_c = 25^{\circ}C$		2272	W
$I_{AR}$	Avalanche current (repetitive and non repetitive)		25	A
$E_{AR}$	Repetitive Avalanche Energy		50	mJ
$E_{AS}$	Single Pulse Avalanche Energy		3000	1117

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$ $T_j = 25^{\circ}C$			600	μА
		$V_{GS} = 0V, V_{DS} = 800V$ $T_j = 125^{\circ}C$			3	
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 64.5A$		60	70	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 15 \text{mA}$	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±500	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	Min	Тур	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		31.1		
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		5.28		nF
$C_{rss}$	Reverse Transfer Capacitance	f = 1MHz		0.96		
$Q_{\mathrm{g}}$	Total gate Charge	$V_{GS} = 10V$		1116		
$Q_{\mathrm{gs}}$	Gate – Source Charge	$V_{Bus} = 500V$		144		пC
$Q_{gd}$	Gate – Drain Charge	$I_{\rm D} = 129 A$		732		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		18		
$T_{\rm r}$	Rise Time	$\begin{aligned} V_{GS} &= 15V \\ V_{Bus} &= 670V \\ I_D &= 129A \\ R_G &= 0.8\Omega \end{aligned}$		12		
$T_{d(off)}$	Turn-off Delay Time			155		ns
$T_{\mathrm{f}}$	Fall Time			40		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		5.4		T
$E_{\text{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 129A, R_G = 0.8\Omega$		3.7		mJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		8.5		т
E <sub>off</sub>	Turn-off Switching Energy	$\begin{array}{c} V_{GS} = 15V, V_{Bus} = 670V \\ I_{D} = 129A, R_{G} = 0.8\Omega \end{array}$		4.7		mJ

#### Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_S$	Continuous Source current		$Tc = 25^{\circ}C$			129	Α
	(Body diode)		$Tc = 80^{\circ}C$			97	A
$V_{\mathrm{SD}}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -129A$				1.3	V
dv/dt	Peak Diode Recovery					18	V/ns
t <sub>rr</sub>	Reverse Recovery Time	1204	$T_j = 25^{\circ}C$			320	ns
·rr	t <sub>rr</sub> Reverse Recovery Time	$I_S = -129A$ $V_R = 670V$	$T_j = 125$ °C			650	115
Q <sub>rr</sub>	Reverse Recovery Charge	$di_S/dt = 600A/\mu s$	$T_j = 25^{\circ}C$		21.6		μC
	Reverse Recovery Charge	,	$T_{i} = 125^{\circ}C$		58.3		μ

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

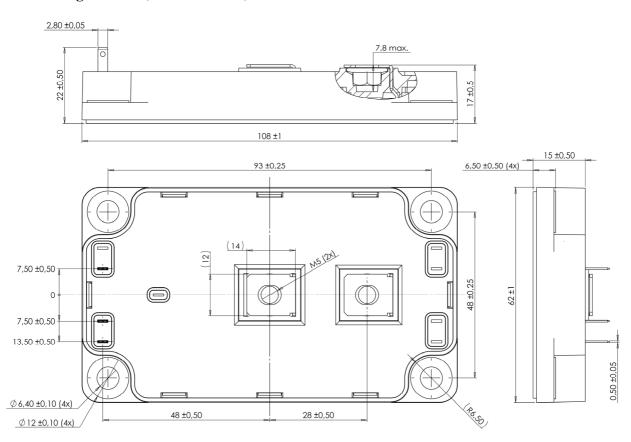
 $I_S \le -129A$   $di/dt \le 700A/\mu s$   $V_R \le V_{DSS}$   $T_j \le 150$ °C



### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance					0.055	°C/W
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		150		
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	11.111
Wt	Package Weight					300	g

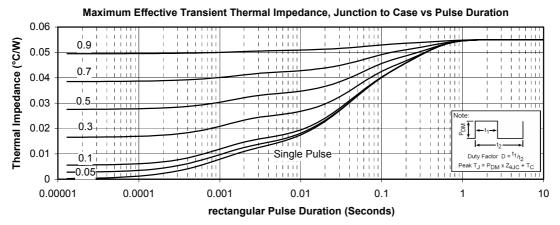
### SP6 Package outline (dimensions in mm)

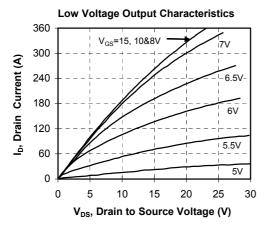


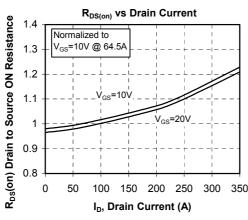
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

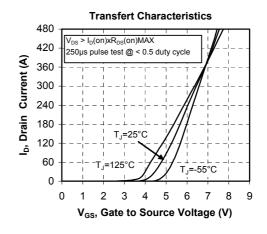


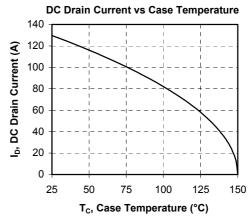
### **Typical Performance Curve**



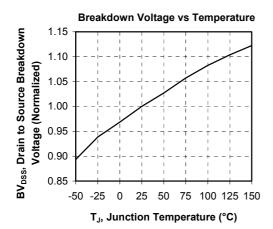


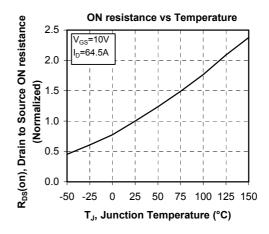


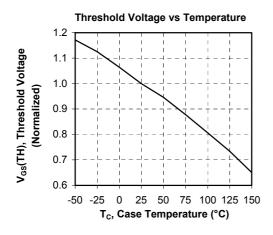


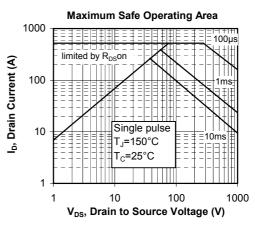


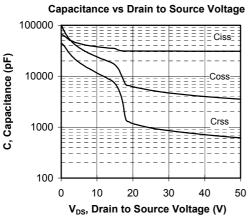


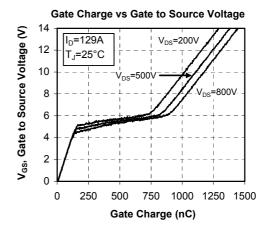




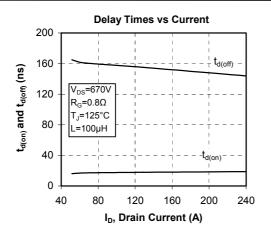


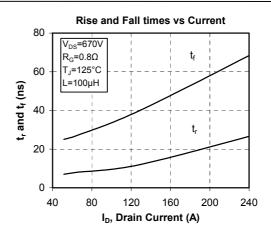


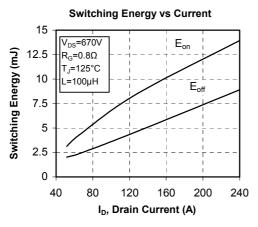


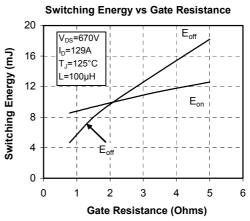


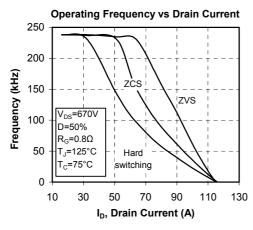


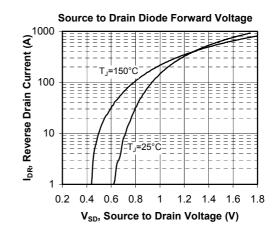














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